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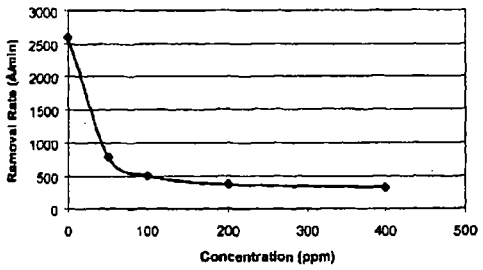
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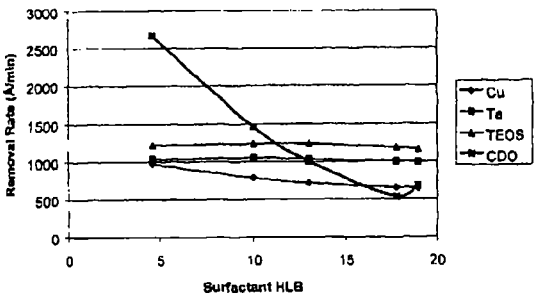
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(54) Title: METHOD FOR CHEMICAL MECHANICAL POLISHING (CMP) OF LOW-K DIELECTRIC MATERIALS

(57) Abstract: The invention provides a method of polishing a substrate containing a low-k dielectric layer comprising (i) contacting the substrate with a chemical-mechanical polishing system comprising (a) an abrasive, a polishing pad, or a combination thereof, (b) an amphiphilic nonionic surfactant, and (c) a liquid carrier, and (ii) abrading at least a portion of the substrate to polish the substrate.





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